V23990-P708-F40-PM

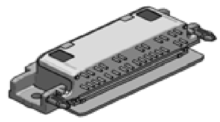
preliminary datasheet

flow90PACK 1 2nd gen — 1200V/15A

Features

- Trench Fieldstop IGBT4 Technology
- Supports designs with 90° mounting angle between heatsink and PCB
- Clip-in PCB mounting
- Clip or screw hetasink mounting

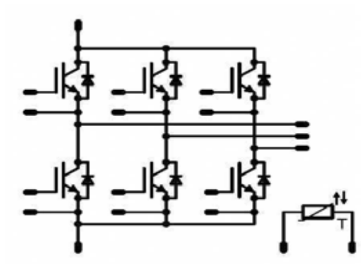
flow90PACK 1 2nd gen



Target Applications

- Motor Drives

Schematic



Types

- V23990-P708-F40-PM

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter IGBT					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	T_j=$T_j$max	T_h=80°C T_c=80°C	21 26	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j$max		60	A
Turn off safe operating area		VCE ≤ 1200V, Tj ≤ Top max		60	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80°C T_c=80°C	65 98	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		10 800	µs V
Maximum Junction Temperature	$T_j$max			175	°C
Inverter FWD					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25°C		1200	V
DC forward current	I_F	T_j=$T_j$max	T_h=80°C T_c=80°C	17 22	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		30	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80°C T_c=80°C	44 67	W
Maximum Junction Temperature	$T_j$max			175	°C

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(Tjmax - 25)	°C
Insulation Properties					
Insulation voltage	V_{is}	t=2s	DC voltage	4000	V
Creepage distance				min 12,7	mm
Clearance				min 12,7	mm
Comparative tracking index	CTI			>200	

Characteristic Values

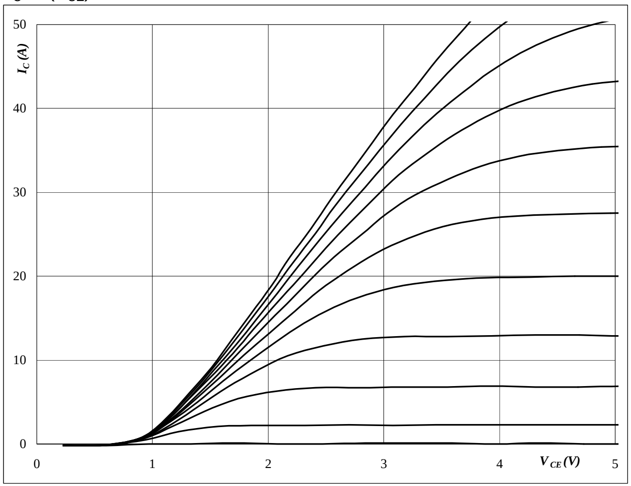
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Inverter IGBT										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0005	Tj=25°C Tj=150°C	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		15	Tj=25°C Tj=150°C	1,3	1,91 2,28	2,3	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		Tj=25°C Tj=150°C			0,002	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			120	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=32 Ω Rgon=32 Ω	±15	600	15	Tj=25°C Tj=150°C		94 94		ns
Rise time	t_r					Tj=25°C Tj=150°C		24 26		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=150°C		196 265		
Fall time	t_f					Tj=25°C Tj=150°C		64 128		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=150°C		1,03 1,50		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=150°C		0,74 1,37		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		900		pF
Output capacitance	C_{oss}							80		
Reverse transfer capacitance	C_{rss}							55		
Gate charge	Q_{Gate}		±15	960	15	Tj=25°C		90		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,47		K/W
Inverter FWD										
Diode forward voltage	V_F				15	Tj=25°C Tj=150°C	1,35	1,82 1,73	2,05	V
Peak reverse recovery current	I_{RRM}	Rgon=32 Ω	±15	600	15	Tj=25°C Tj=150°C		15 17		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=150°C		271 450		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=150°C		1,51 2,70		μC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=150°C		96 56		A/μs
Reverse recovered energy	Erec					Tj=25°C Tj=150°C		0,57 1,07		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2,16		K/W
Thermistor										
Rated resistance	R					Tj=25°C		22000		Ω
Deviation of R100	ΔR/R	R100=1486 Ω				Tc=100°C	-5		5	%
Power dissipation	P					Tc=100°C		200		mW
Power dissipation constant						Tj=25°C		2		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				Tj=25°C		3950		K
B-value	$B_{(25/100)}$	Tol. ±3%				Tj=25°C		3996		K
Vincotech NTC Reference						Tj=25°C			B	

Output Inverter

Figure 1	Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



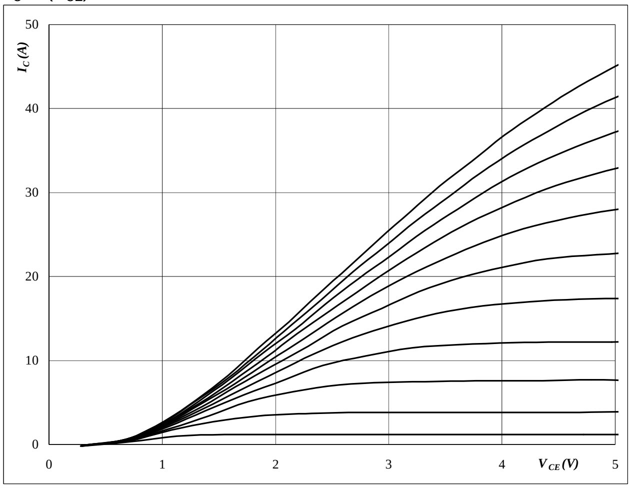
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2	Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



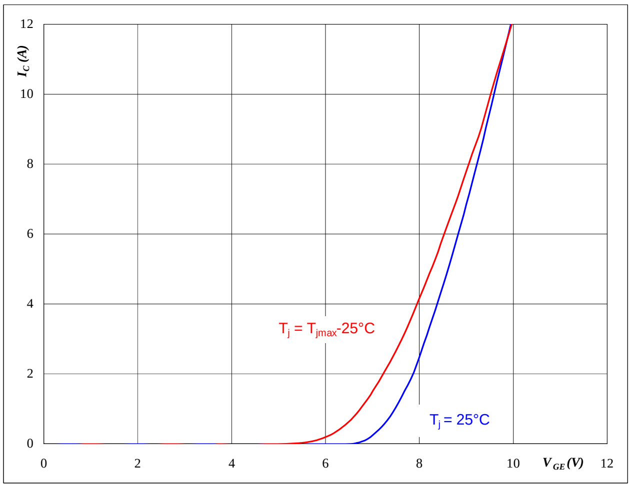
At

t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3	Output inverter IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



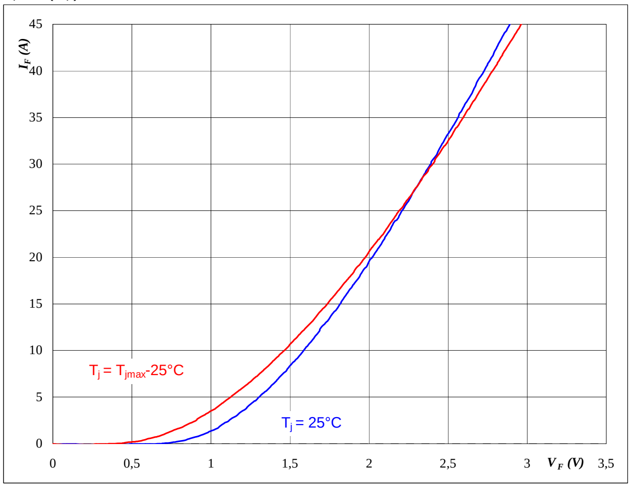
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4	Output inverter FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

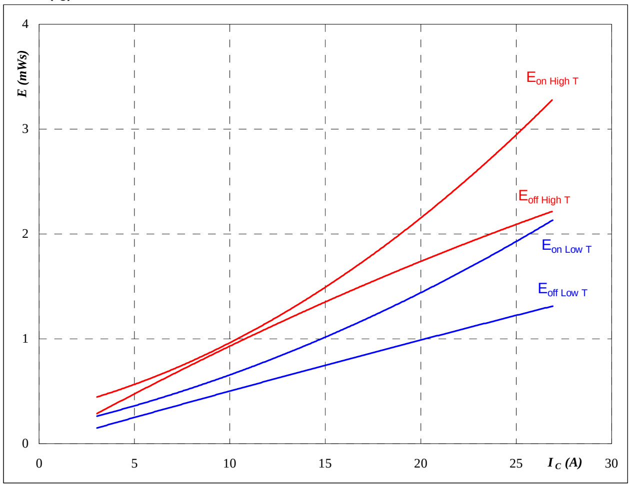
t_p =	250	µs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



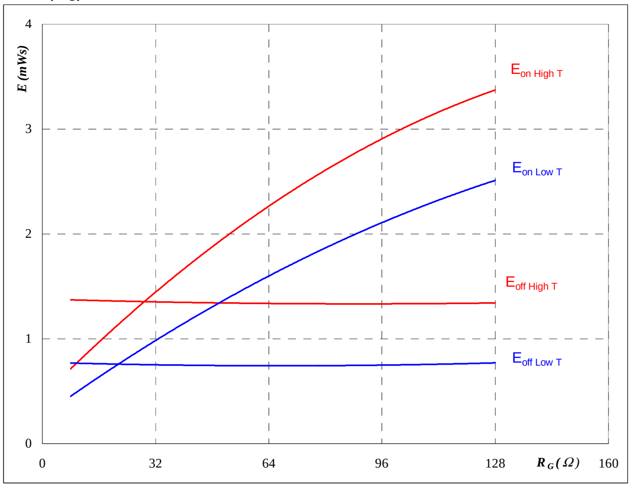
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



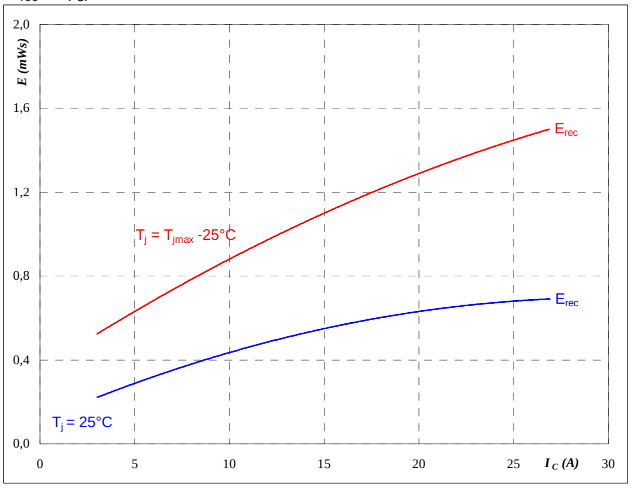
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 7 Output inverter FWD

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_C)$



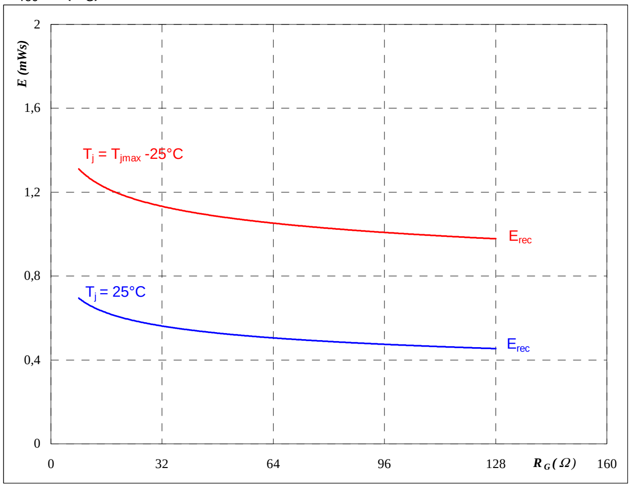
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 8 Output inverter FWD

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

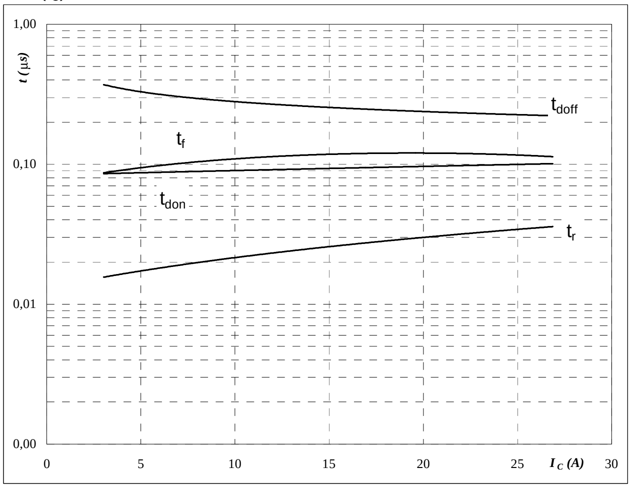
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

t = f(I_C)



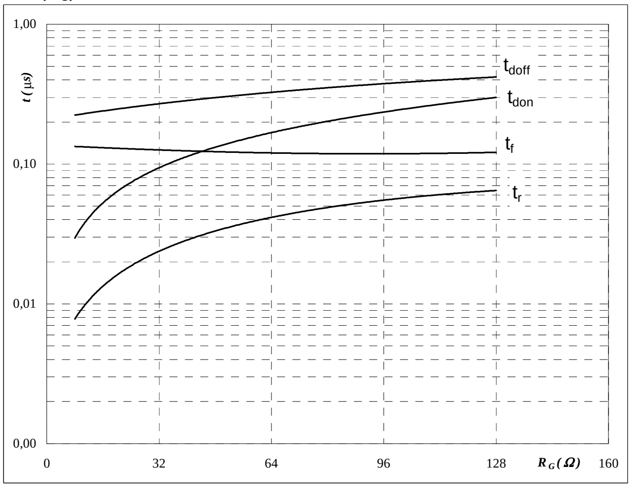
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



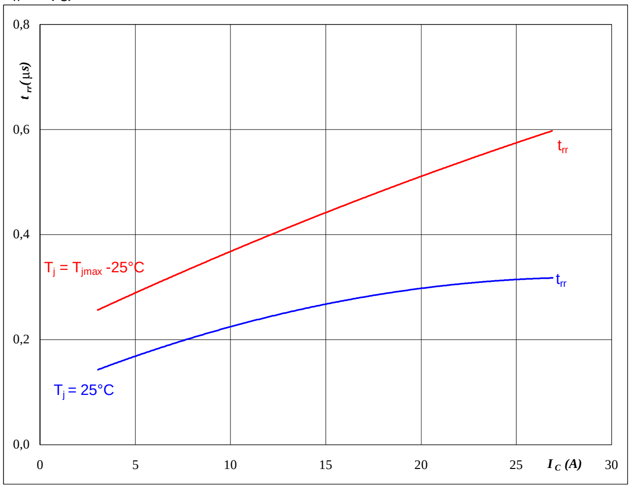
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 11 Output inverter FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



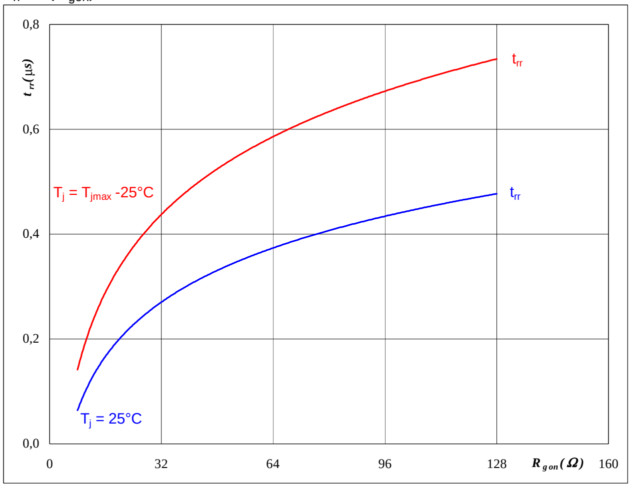
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 12 Output inverter FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

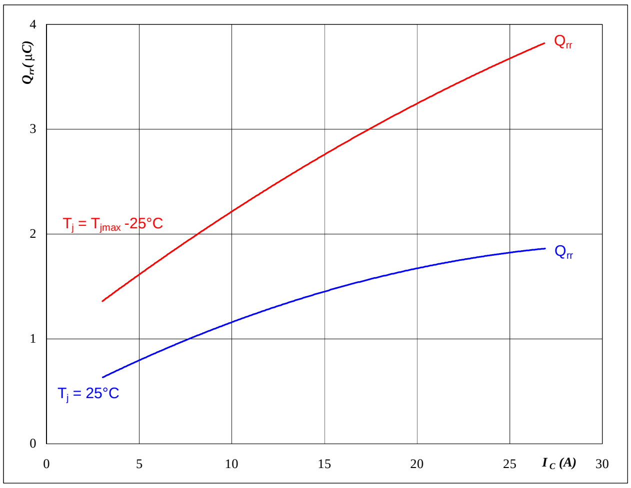
T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Output Inverter

Figure 13	Output inverter FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



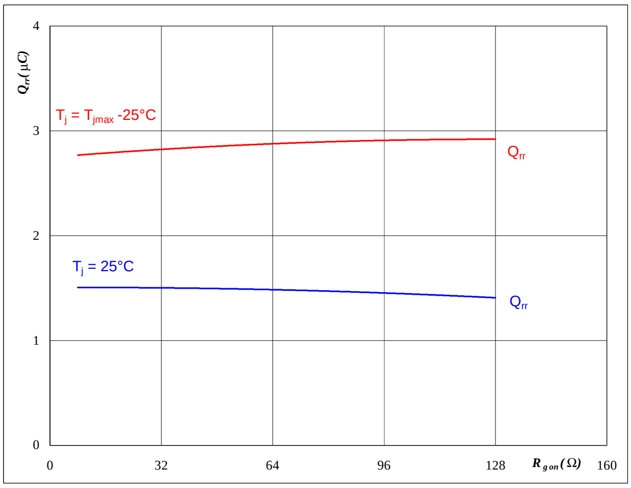
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 14	Output inverter FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



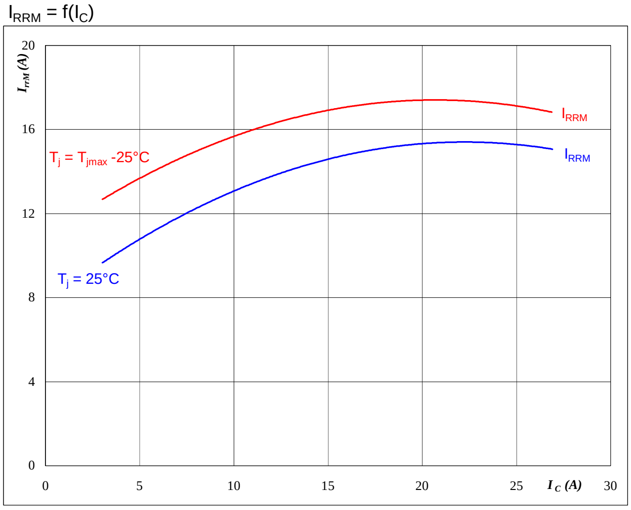
At

T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Figure 15	Output inverter FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



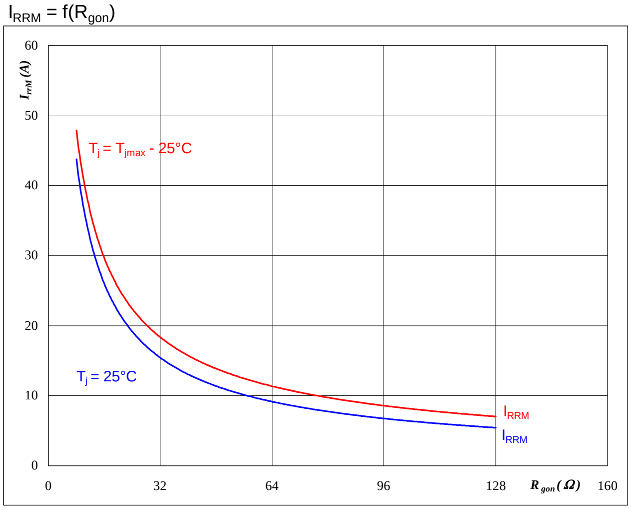
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 16	Output inverter FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

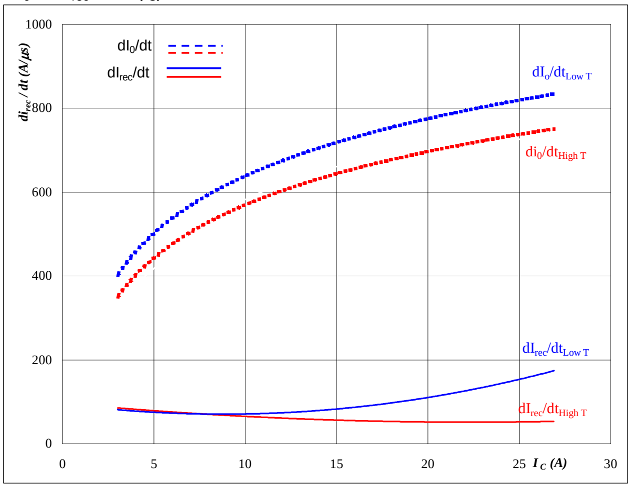
T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Output Inverter

Figure 17 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



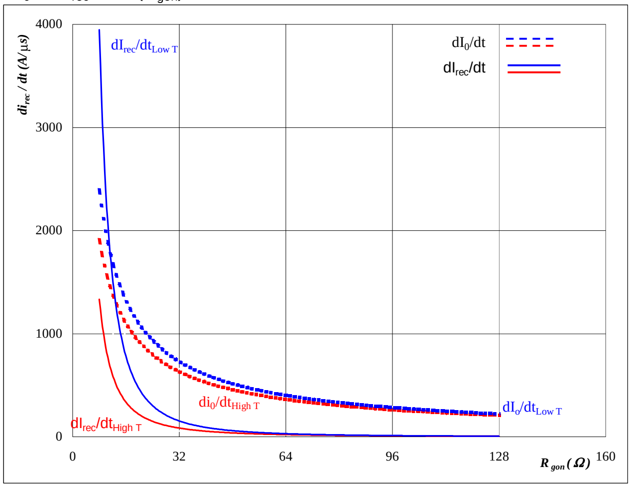
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 18 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



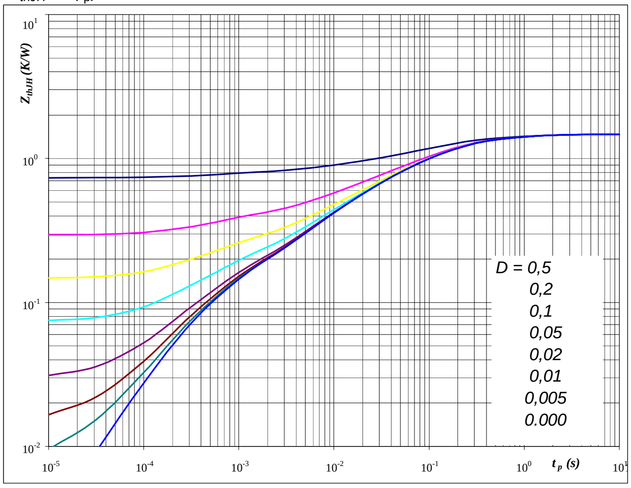
At

T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Figure 19 Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



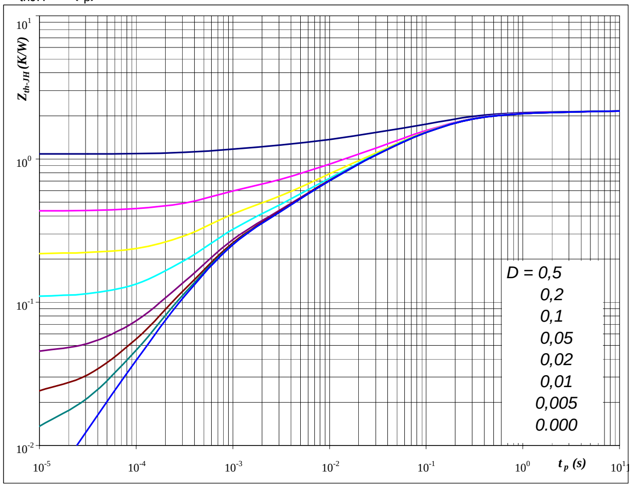
At

D =	t_p / T	
R_{thJH} =	1,47	K/W

Figure 20 Output inverter FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T	
R_{thJH} =	2,16	K/W

IGBT thermal model values

Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,19	8,2E-01	0,15	6,7E-01
0,62	1,3E-01	0,50	1,1E-01
0,38	2,7E-02	0,31	2,2E-02
0,17	4,9E-03	0,14	3,9E-03
0,10	4,2E-04	0,08	3,4E-04

FWD thermal model values

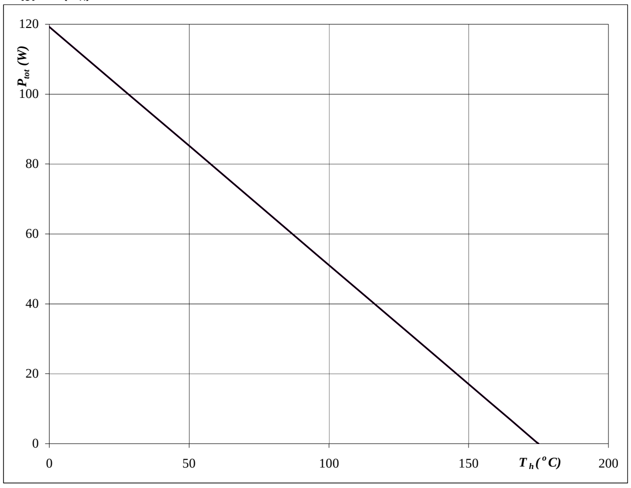
Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,10	3,2E+00	0,08	2,6E+00
0,42	3,0E-01	0,34	2,4E-01
0,91	7,3E-02	0,74	5,9E-02
0,48	8,7E-03	0,39	7,0E-03
0,24	7,1E-04	0,20	5,7E-04

Output Inverter

Figure 21	Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



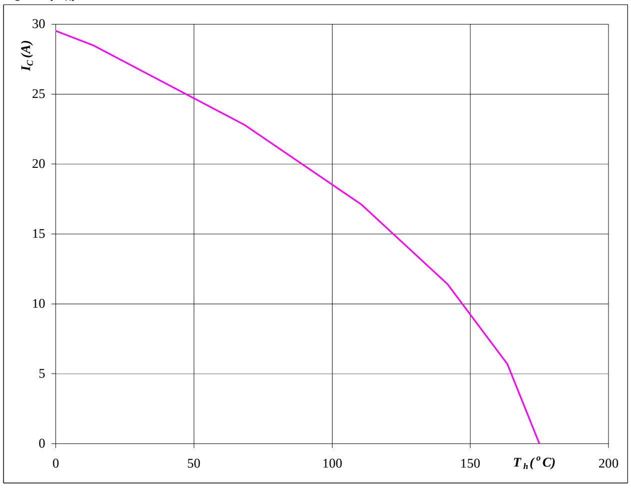
At

T_j =	175	°C

Figure 22	Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



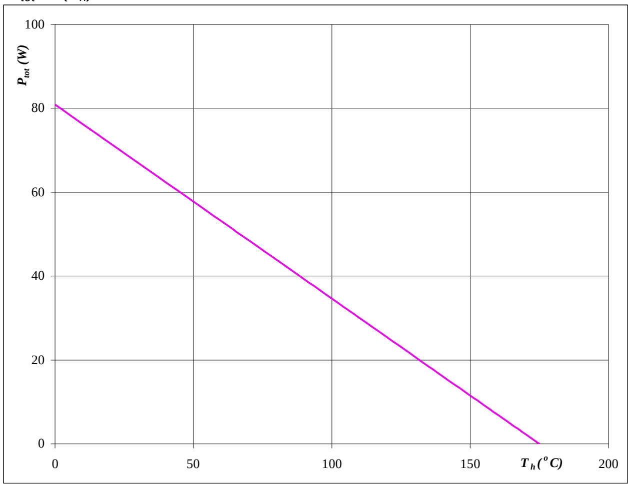
At

T_j =	175	°C
V_{GE} =	15	V

Figure 23	Output inverter FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



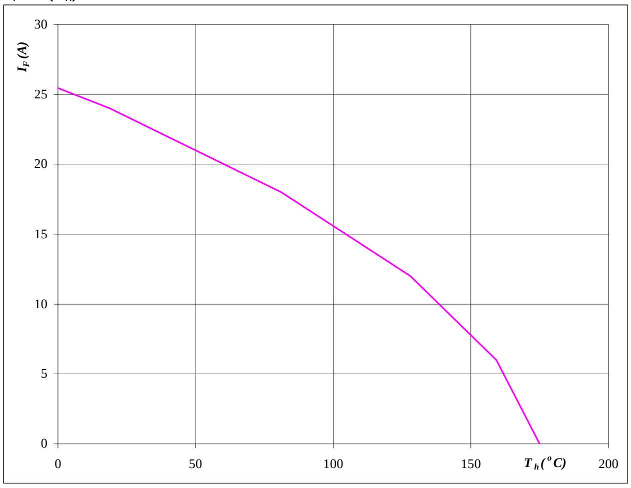
At

T_j =	175	°C

Figure 24	Output inverter FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

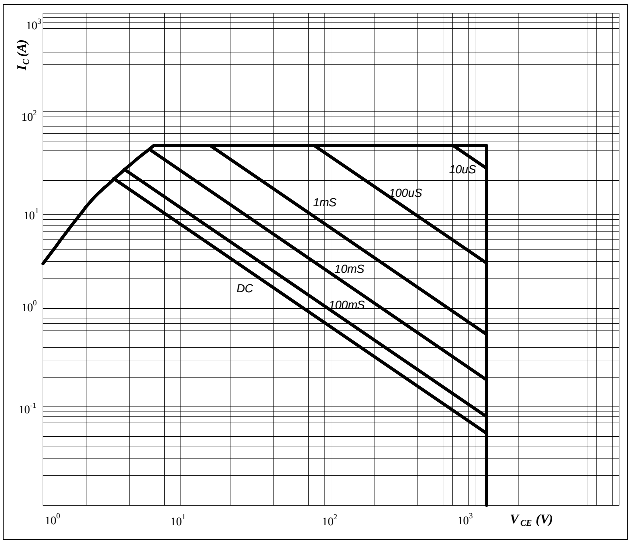
T_j =	175	°C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



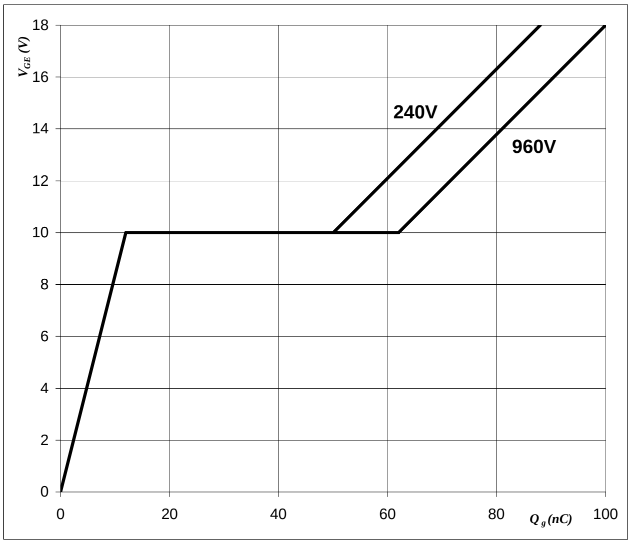
At

D =	single pulse	
T_h =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26 Output inverter IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_{GE})$



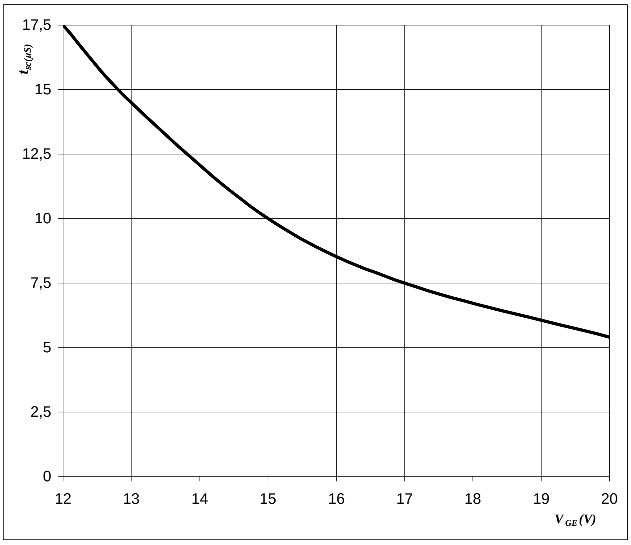
At

I_C =	15	A

Figure 27 Output inverter IGBT

Short circuit withstand time as a function of gate-emitter voltage

$t_{sc} = f(V_{GE})$



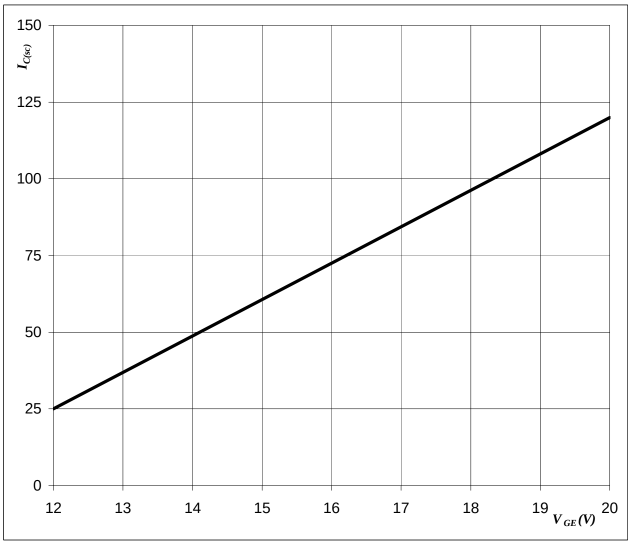
At

V_{CE} =	1200	V
T_j ≤	175	ºC

Figure 28 Output inverter IGBT

Typical short circuit collector current as a function of gate-emitter voltage

$V_{GE} = f(Q_{GE})$



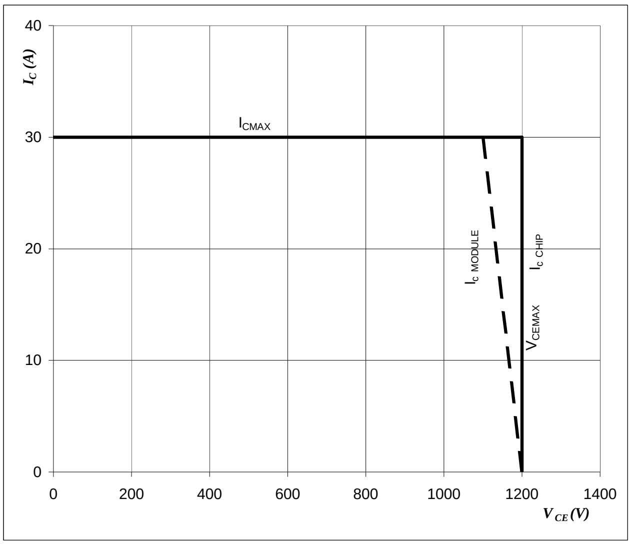
At

V_{CE} ≤	1200	V
T_j =	175	ºC

Figure 29 IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

$U_{ccminus}$=U_{ccplus}

Switching mode : 3phase SPWM

Thermistor

Figure 1	Thermistor

Typical NTC characteristic
as a function of temperature
$R_T = f(T)$

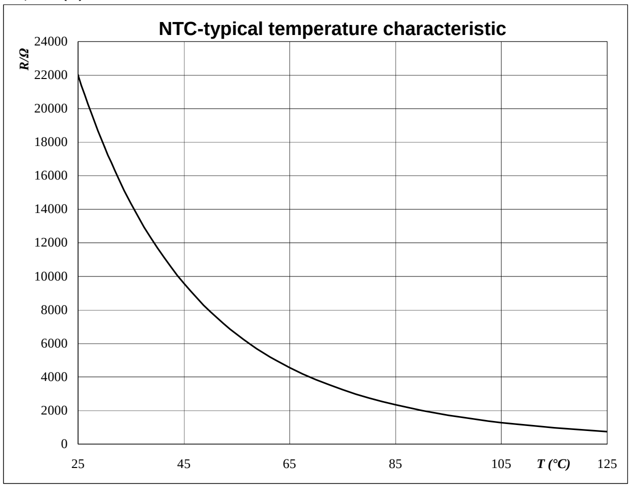


Figure 2	Thermistor

Typical NTC resistance values

$$R(T) = R_{25} \cdot e^{\left(B_{25/100} \cdot \left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right)} \quad [\Omega]$$

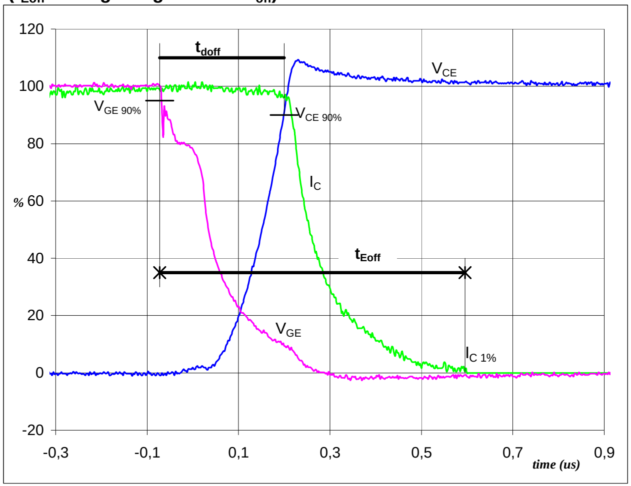
Switching Definitions Output Inverter

General conditions

T_j	=	150 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

Figure 1 Output inverter IGBT

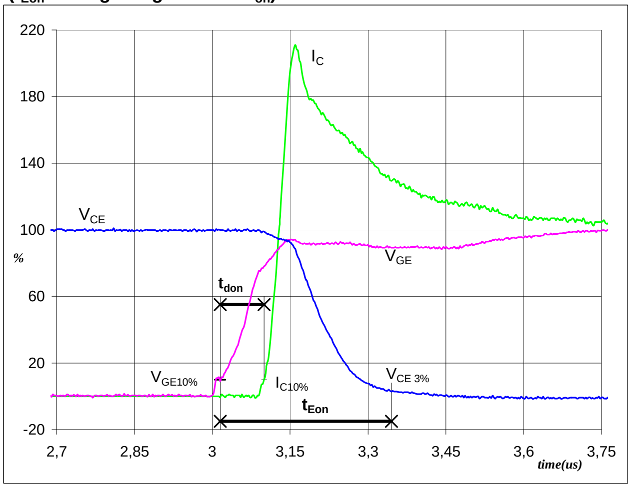
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	15	A
t_{doff} =	0,27	µs
t_{Eoff} =	0,67	µs

Figure 2 Output inverter IGBT

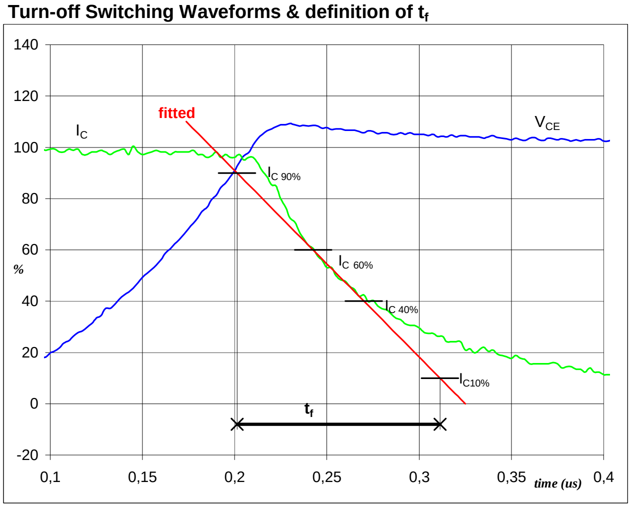
Turn-on Switching Waveforms & definition of tdon, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	15	A
t_{don} =	0,09	µs
t_{Eon} =	0,33	µs

Figure 3 Output inverter IGBT

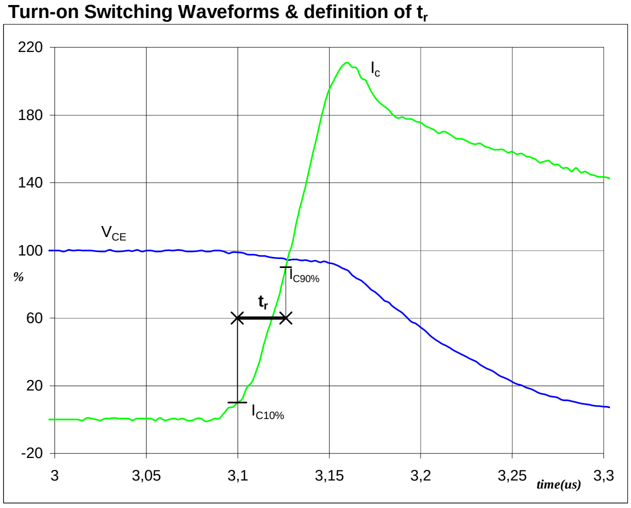
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	15	A
t_f =	0,13	µs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

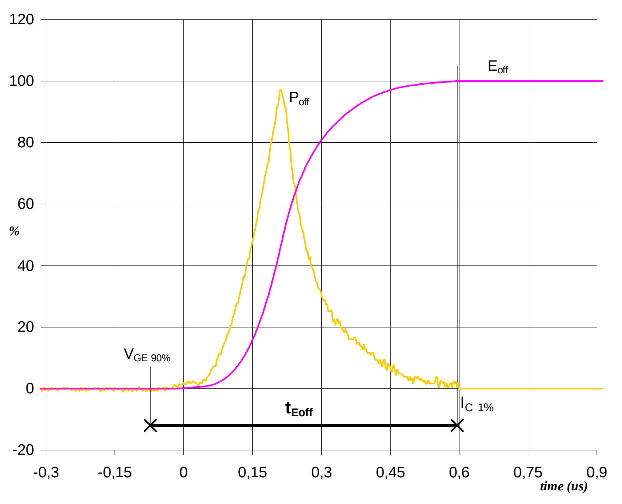


V_C (100%) =	600	V
I_C (100%) =	15	A
t_r =	0,03	µs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

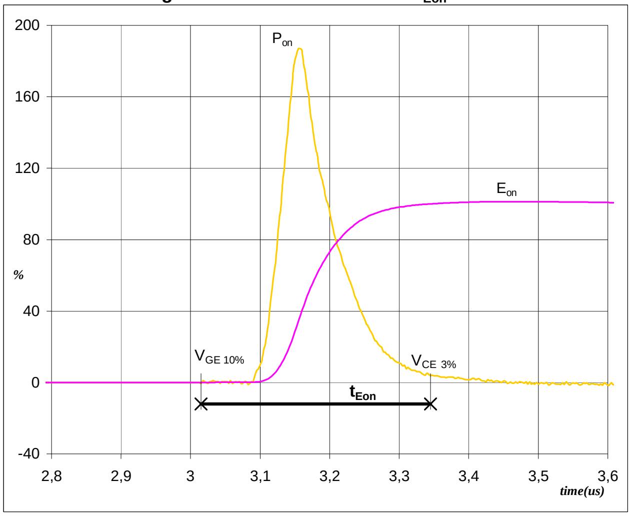
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) = 9,08 kW
E_{off} (100%) = 1,37 mJ
t_{Eoff} = 0,67 µs

Figure 6 Output inverter IGBT

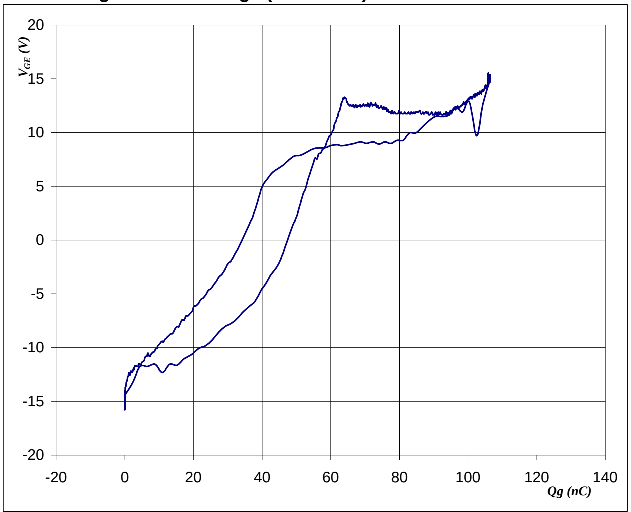
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) = 9,08 kW
E_{on} (100%) = 1,50 mJ
t_{Eon} = 0,33 µs

Figure 7 Output inverter FWD

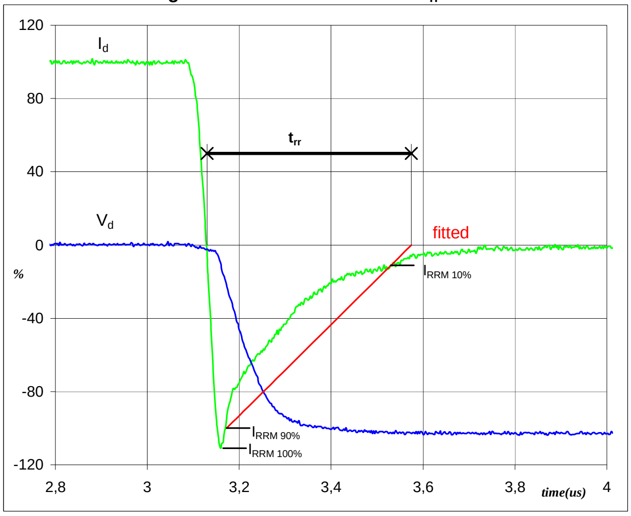
Gate voltage vs Gate charge (measured)



V_{GEoff} = -15 V
V_{GEon} = 15 V
V_C (100%) = 600 V
I_C (100%) = 15 A
Q_g = 106,36 nC

Figure 8 Output inverter IGBT

Turn-off Switching Waveforms & definition of t_{rr}

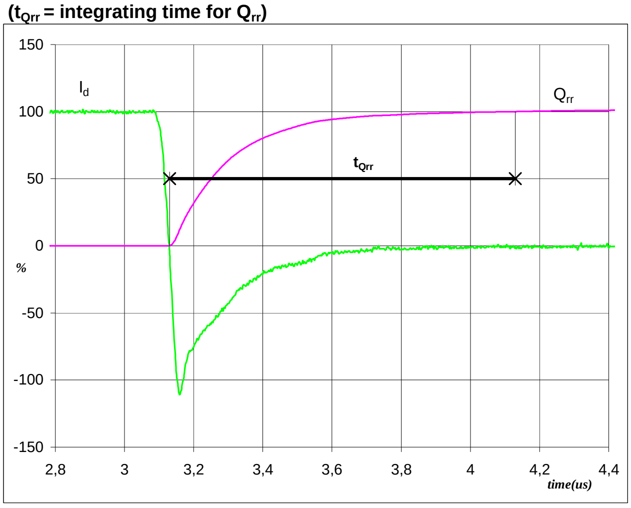


V_d (100%) = 600 V
I_d (100%) = 15 A
I_{RRM} (100%) = -17 A
t_{rr} = 0,45 µs

Switching Definitions Output Inverter

Figure 9 Output inverter FWD

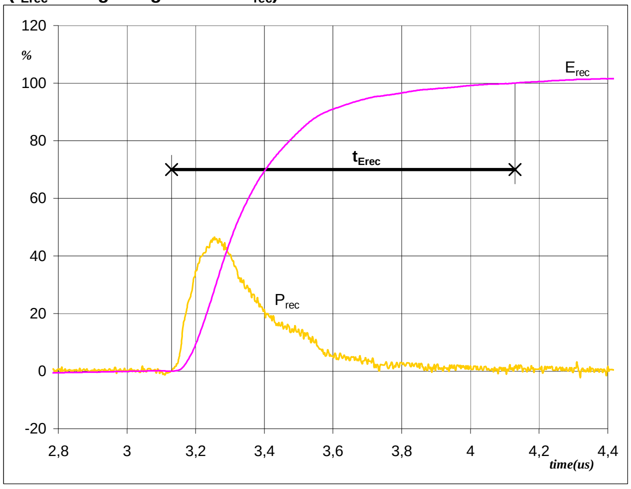
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	15	A
Q_{rr} (100%) =	2,70	μC
t_{Qrr} =	1,00	μs

Figure 10 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	9,08	kW
E_{rec} (100%) =	1,07	mJ
t_{Erec} =	1,00	μs

Ordering Code and Marking - Outline - Pinout

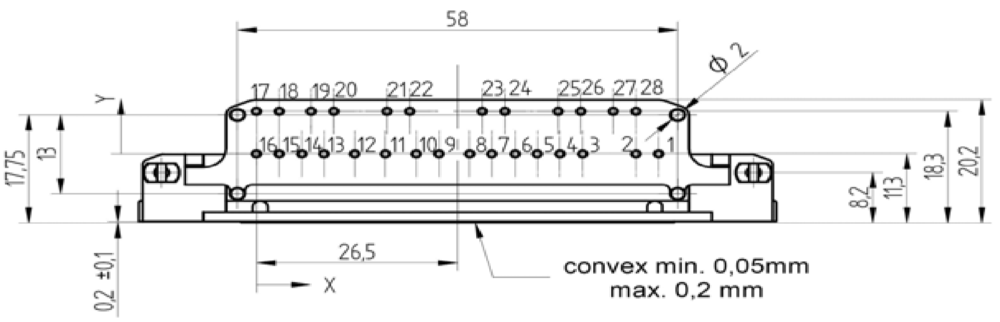
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
without thermal paste 12mm housing	V23990-P708-F40-PM	P708F40	P708F40

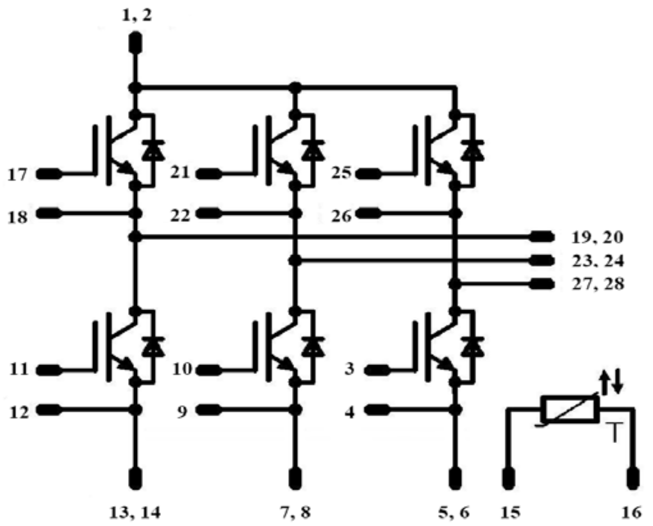
Outline

Pin Table

Pin	X	Y
1	53	0
2	50	0
3	43	0
4	40	0
5	37	0
6	34,1	0
7	31	0
8	28,1	0
9	24,05	0
10	21,05	0
11	17	0
12	12,95	0
13	8,9	0
14	6	0
15	3	0
16	0	0
17	0	7
18	3	7
19	7,2	7
20	10,2	7
21	17,2	7
22	20,2	7
23	29,75	7
24	32,75	7
25	39,75	7
26	42,75	7
27	47	7
28	50	7



Pinout



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Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
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